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		Application Number	10/500,214		
		Filing Date	June 28, 2004		
		First Named Inventor	Takuya SUGAWARA		
		Art Unit	2812		
		Examiner Name	Francine Young		
Sheet	1	of	1	Attorney Docket Number	010986.55104US

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
	AA	Y. AOKI, ET AL., "In Situ Substrate Surface Cleaning by Low-Energy Ion Bombardment for High Quality Thin Film Formation", J. Vac. Sci. Technol. A, March/April 1993, pp. 307-313, vol. 11 no. 2, American Vacuum Society	
	AB	KATSUYUKI SEKINE, ET AL., "Silicon Nitride Film Growth for Advanced Gate Dielectric at Low Temperature Employing High-Density and low-Energy Ion Bombardment", J. Vac. Sci. Technol. A, September/October 1999, pp. 3129-3133, vol. 17, No. 5, American Vacuum Society	
	AC	KOTARO MIYATANI, ET AL., "A New Plasma Dry Cleaning Method Applied to Contact and Gate Pre Cleaning", Extended Abstracts of the 2002 International Conference on Solid State Devices and Materials, 2002, pp. 196-197, Nagoya	
	AD	N. SANO, ET AL., "Improvement of SiO <sub>2</sub> /Si Interface by Low-Temperature Annealing in Wet Atmosphere", Appl. Phys. Lett., April 17, 1995, pp. 2107-2109, vol. 66, no. 16, American Institute of Physics	
	AE	D. TCHIKATILOV, ET AL., "Improvement of SiGe Oxide Grown by Electron Cyclotron Resonance Using H <sub>2</sub> O Vapor Annealing", Appl. Phys. Lett., October 21, 1996, pp. 2578-2580, vol. 69, no. 17, American Institute of Physics	
	AF	TAKUYA SUGAWARA, ET AL., "Characterization of Ultra Thin Oxynitride Formed by Radical Nitridation with Slot Plane Antenna Plasma", Extended Abstracts of the 2002 International Conference on Solid Devices and Materials, 2002, pp. 714-715, Nagoya	
	AG	AKIKO NARA, ET AL., "A Guideline for Accurate Two-Frequency Capacitance Measurement for ultra-Thin Gate Oxides", Extended Abstracts of the 2002 International Conference on Solid Devices and Materials, 2002, pp. 452-453, Sendai	
	AH	ATSUHIRO TSUKUNE, ET AL., "Cu Damascene Formation Process", The 8 <sup>th</sup> Semiconductor Process Symposium, September 20, 1999, pp. 71-79	
	AI	T. NGAL ET AL., "Improving SiO <sub>2</sub> /SiGe Intface of SiGe p-metal-oxide-silicon field-effect transistors using water vapor annealing", March 11, 2002, pp. 1773-1775	

Examiner Signature		Date Considered	
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